

ABSTRACT OF THE DISCLOSURE

A process for forming portions of a compound material within an electronic circuit includes the formation of a cavity having at least one opening facing onto an access  
5 surface. The cavity furthermore has an internal wall with at least one region made of an initial material (for example, silicon). A metal is deposited close to the region of initial material. The circuit is then heated to form a portion of the compound material (for example, a  
10 silicide) in the region of initial material inside the cavity. The compound material is formed from elements of the initial material and from some of the metal deposited. The excess metal that has not formed some of the compound material is then removed from the cavity.